



FQA10N80C_F109 Information

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Part Number FQA10N80C_F109

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

Description MOSFET N-CH 800V 10A TO-3P

Package TO-3P-3, SC-65-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FQA10N80C_F109 Specifications

Manufacturer Part Number FQA10N80C_F109 Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-3P-3, SC-65-3 Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 58nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2800pF @ 25V Vgs (Max) 230V FET Feature - Power Dissipation (Max) 240W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P-3, SC-65-3 Package / Case TO-3P-3, SC-65-3		
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2800pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)240W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Series	QFET?
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Current - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2800pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)240W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2800pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)240W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Drain to Source Voltage (Vdss)	800V
Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 58nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2800pF @ 25V Vgs (Max) ±30V FET Feature Power Dissipation (Max) 240W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Current - Continuous Drain (Id) @ 25°C	10A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature John Capacitance (Ciss) (Max) @ Id, Vgs 1.1 Ohm @ 5A, 10V Operating Temperature John Capacitance (Ciss) (Max) @ Id, Vgs Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 2800pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)240W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Gate Charge (Qg) (Max) @ Vgs	58nC @ 10V
FET Feature - Power Dissipation (Max) 240W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Input Capacitance (Ciss) (Max) @ Vds	2800pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs1.1 Ohm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Power Dissipation (Max)	240W (Tc)
Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Rds On (Max) @ Id, Vgs	1.1 Ohm @ 5A, 10V
Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-3P-3, SC-65-3	Mounting Type	Through Hole
	Supplier Device Package	TO-3P
Report errors?	Package / Case	TO-3P-3, SC-65-3
		Report errors?

FQA10N80C_F109 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQA10N80C_F109 Payment Methods



















FQA10N80C_F109 Shipping Methods













If you have any question about FQA10N80C_F109, please do not hesitate to contact us!

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